

WHAT IS CLAIMED IS:

[1] A wafer support that supports a semiconductor substrate in a reaction chamber, into which a
5 reaction gas is supplied,
the wafer support being arranged so that a predetermined gas flows into a predetermined space that is formed between a semiconductor substrate setting surface and the semiconductor substrate and
10 is connected to an outer surface other than the semiconductor substrate setting surface.

[2] The wafer support according to Claim 1,
wherein
a supply source of the predetermined gas is formed
15 at a substantially central region of the wafer support.

[3] The wafer support according to Claim 1 or 2,
wherein
the predetermined gas is hydrogen gas.

20 [4] The wafer support according to Claim 1 or 2,
wherein
the predetermined gas is an inert gas.

[5] A semiconductor substrate processing method
for setting a semiconductor substrate on a wafer
25 support disposed inside a reaction chamber and
supplying a reaction gas into the reaction chamber
to form a thin film on the semiconductor substrate,

the semiconductor substrate processing method being characterized in that the thin film is formed on the semiconductor substrate while making a predetermined gas flow into a predetermined space that is formed between a semiconductor substrate setting surface of the wafer support and the semiconductor substrate and is connected to an outer surface other than the semiconductor substrate setting surface.

10 [6] The semiconductor substrate processing method according to Claim 5,

wherein the predetermined gas is supplied from a substantially central region of the wafer support.

[7] The semiconductor substrate processing method
15 according to Claim 5 or 6,

the predetermined gas is hydrogen gas.

[8] The semiconductor substrate processing method according to Claim 5 or 6,

the predetermined gas is an inert gas.